MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM3J168F

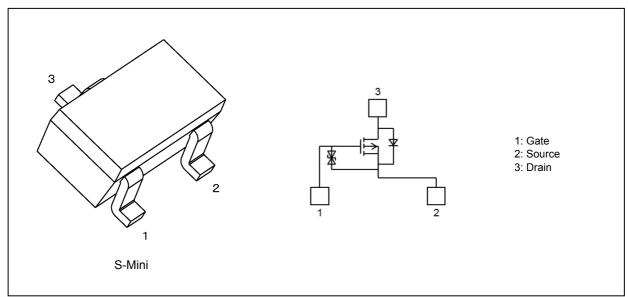
### 1. Applications

- High-Speed Switching
- Analog Switches
- Interfacing

### 2. Features

- (1) AEC-Q101 qualified (Please see the orderable part number list)
- (2) 4.0 V drive
- (3) Low drain-source on-resistance
  - :  $\mathrm{R}_{\mathrm{DS(ON)}}$  = 1.6  $\Omega$  (typ.) (V\_{\mathrm{GS}} = -4.0 V)
  - $\mathrm{R}_{\mathrm{DS(ON)}}$  = 1.4  $\Omega$  (typ.) (V\_{\mathrm{GS}} = -4.5 V)
  - $\mathrm{R}_{\mathrm{DS(ON)}} = 1.3 \; \Omega$  (typ.) (V\_{\mathrm{GS}} = -10 \; \mathrm{V})

### 3. Packaging and Internal Circuit



### 4. Orderable part number

Orderable part number	AEC-Q101		Note			
SSM3J168F,LF	—		General Use			
SSM3J168F,LXGF	YES	(Note 1)	Unintended Use (Note			
SSM3J168F,LXHF	YES		Automotive Use			

Note 1: For more information, please contact our sales or use the inquiry form on our website.

### 5. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25$ °C)

Character	istics		Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	-60	V
Gate-source voltage			V <sub>GSS</sub>	-20/+10	7
Drain current (DC)	·	(Note 1)	Ι <sub>D</sub>	-400	mA
Drain current (pulsed)	·	(Note 1)	I <sub>DP</sub>	-800	7
Power dissipation		(Note 2)	PD	600	mW
Power dissipation	t ≤ 1s	(Note 2)		1200	]
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Device mounted on a 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm<sup>2</sup>)

- Note: This transistor is sensitive to electrostatic discharge and should be handled with care.
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

### 6. Electrical Characteristics

### 6.1. Static Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = -16 V/+10 V	_	—	±10	μA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0 V		_	-10	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 0 V	-60	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 10 V	-50	_	_	
Gate threshold voltage	(Note 2)	V <sub>th</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA	-0.8	_	-2.0	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	$I_{\rm D}$ = -100 mA, $V_{\rm GS}$ = -4.0 V	_	1.6	2.0	Ω
			I <sub>D</sub> = -100 mA, V <sub>GS</sub> = -4.5 V	_	1.4	1.9	
			I <sub>D</sub> = -200 mA, V <sub>GS</sub> = -10 V	_	1.3	1.55	

Note 1: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

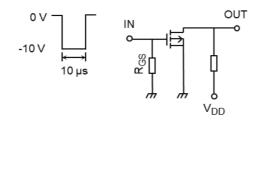
Note 2: Let V<sub>th</sub> be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (-1 mA for this device). Then, for normal switching operation, V<sub>GS(ON)</sub> must be higher than V<sub>th</sub>, and V<sub>GS(OFF)</sub> must be lower than V<sub>th</sub>. This relationship can be expressed as: V<sub>GS(OFF)</sub> < V<sub>th</sub> < V<sub>GS(ON)</sub>. Take this into consideration when using the device.

Note 3: Pulse measurement.

#### 6.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	$V_{DS}$ = -10 V , $V_{GS}$ = 0 V,	_	82	—	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	5.5	—	
Output capacitance	C <sub>oss</sub>			13	_	
Switching time (turn-on time)	t <sub>on</sub>	V <sub>DD</sub> = -30 V, I <sub>D</sub> = -0.1 A, V <sub>GS</sub> = 0 to -10 V, R <sub>G</sub> = 50 Ω		4.3		ns
Switching time (turn-off time)	t <sub>off</sub>	$\begin{array}{l} Duty \leq 1 \ \%, V_{IN} \text{:} \ t_r, \ t_f < 5 \ ns, \\ Common \ source, \ See \ Chapter \ 6.3. \end{array}$	_	31.7	_	

### 6.3. Switching Time Test Circuit



 $\begin{array}{c} 0 \\ V \\ -10 \\ V \\ V_{DS(ON)} \\ V_{DD} \\ \end{array}$ 

Fig. 6.3.1 Switching Time Test Circuit

Fig. 6.3.2 Input Waveform/Output Waveform

### 6.4. Gate Charge Characteristics (Unless otherwise specified, $T_a = 25$ °C)

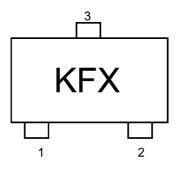
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V <sub>DD</sub> = -48 V, I <sub>D</sub> = -0.4 A,	—	3.0	—	nC
Gate-source charge 1	Q <sub>gs1</sub>	V <sub>GS</sub> = -10 V	_	0.4	—	
Gate-drain charge	Q <sub>gd</sub>		_	1.1	_	

### 6.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25$ °C)

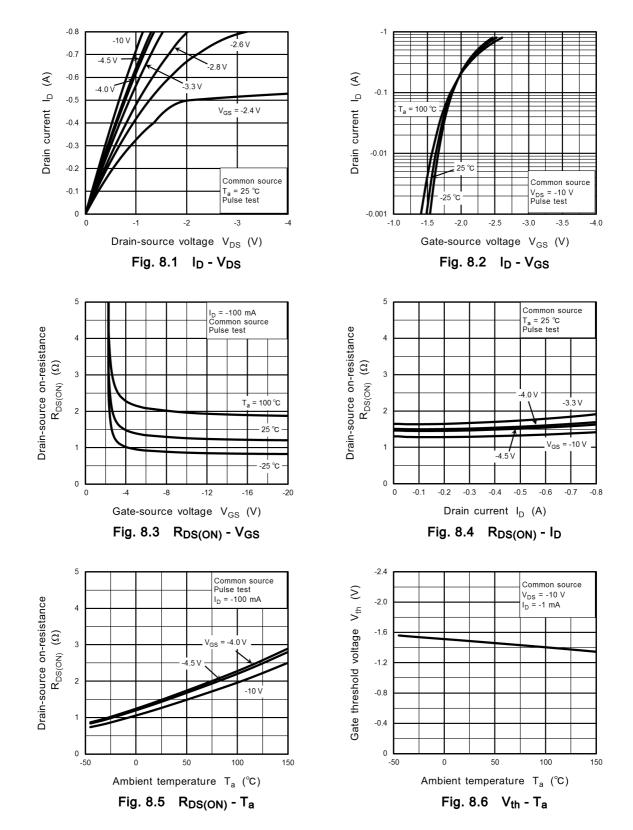
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	V <sub>DSF</sub>	$I_{D}$ = 400 mA, $V_{GS}$ = 0 V	_	0.87	1.2	V

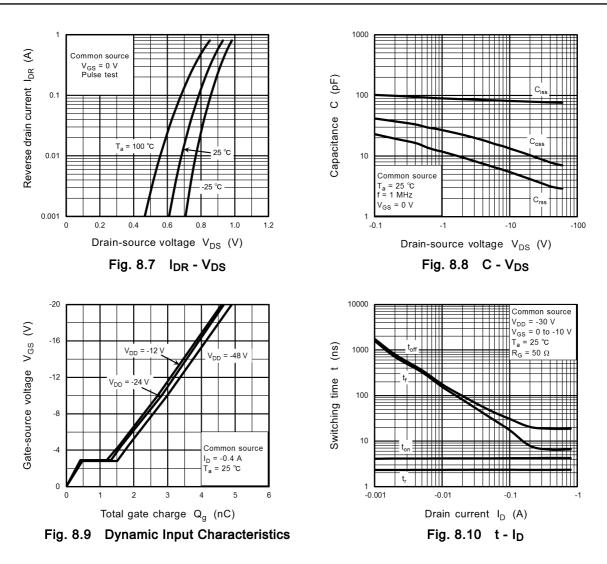
Note 1: Pulse measurement.

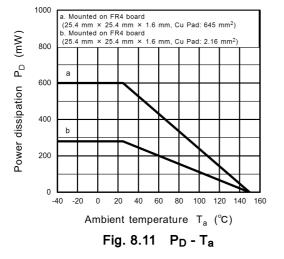
### 7. Marking



### 8. Characteristics Curves (Note)





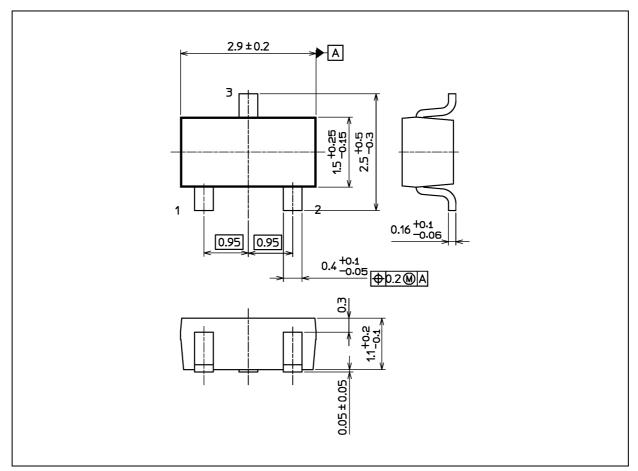


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### SSM3J168F

### Package Dimensions

Unit: mm



Weight: 12 mg (typ.)

	Package Name(s)
JEDEC: SOT-346	
Nickname: S-Mini	

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